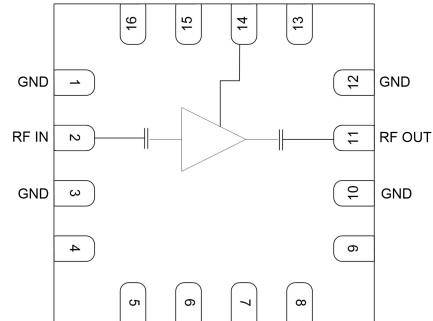


## GaAs MMIC Low Noise Amplifier Chip, 17 - 23 GHz

### Performance characteristics

- Frequency Range: 17 - 23 GHz
- Small signal gain: 25dB
- Gain flatness:  $\pm 0.8$ dB
- Noise figure: 1.6dB Typ.
- P -1 dB: 3dBm
- Power supply: + 5V /15mA
- 50Ohm input / output
- 100% on-wafer testing
- Chip size: QFN 3X3

### Block Diagram



### Product Introduction

GLA-1723D-PQ3 is a broadband low noise amplifier chip with a frequency range of 17GHz~23GHz, a small signal gain of 25dB, and an in-band noise figure of 1.6dB. GLA-1723D-PQ3 is powered by a single +5V power supply. This chip is packaged in a 3 x 3 mm plastic surface mount package, and the surface of the pin pad is tinned, which is suitable for reflow soldering installation.

### Use limit parameters

Maximum drain voltage	+7V
Maximum input power	+20dBm
Operating temperature	-55 ~ + 125 °C
Storage temperature	-65 ~ +150°C

Exceeding any of these maximum limits may cause permanent damage.

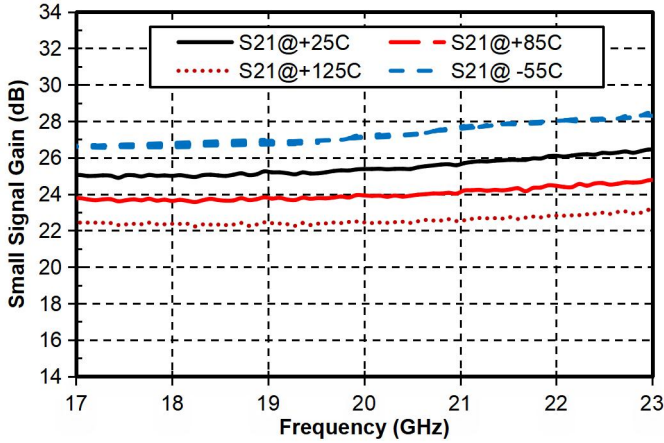
### Electrical performance parameters ( TA = +25°C, Vd = +5V )

Index	Minimum	Typical Value	Maximum	Unit
Frequency Range	17-23			G Hz
Small Signal Gain	-	25	-	dB
Gain Flatness	-	$\pm 0.8$	-	dB
Noise Figure	-	1.6	-	dB
P -1dB	-	3	-	dBm
Psat	-	4.5	-	dBm
Input return loss	-	20	-	dB
Output return loss	-	14	-	dB
Quiescent Current	-	15	-	mA

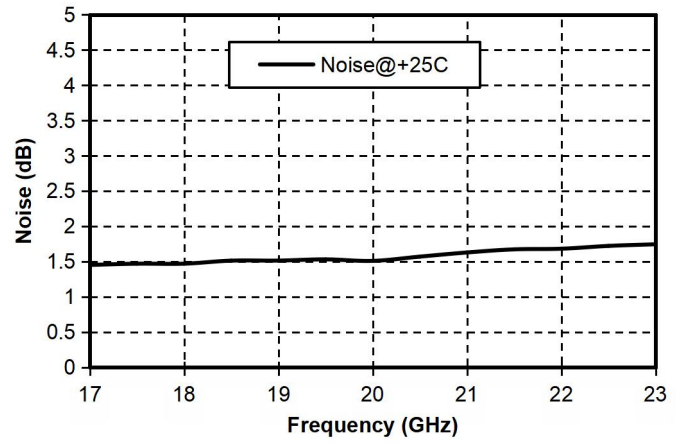
## GaAs MMIC Low Noise Amplifier Chip, 17 - 23 GHz

Main index test curve

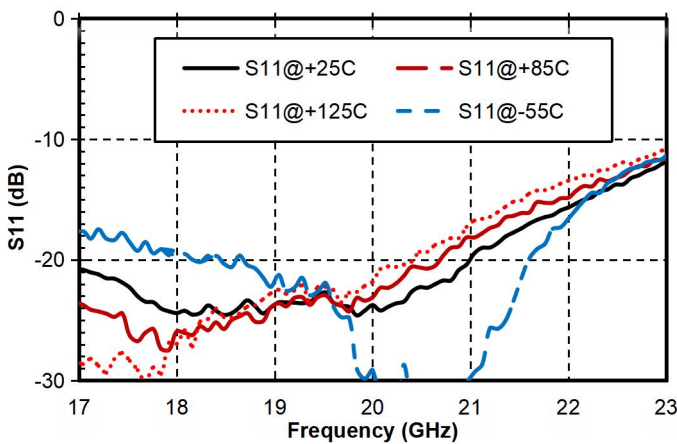
Gain vs. Frequency



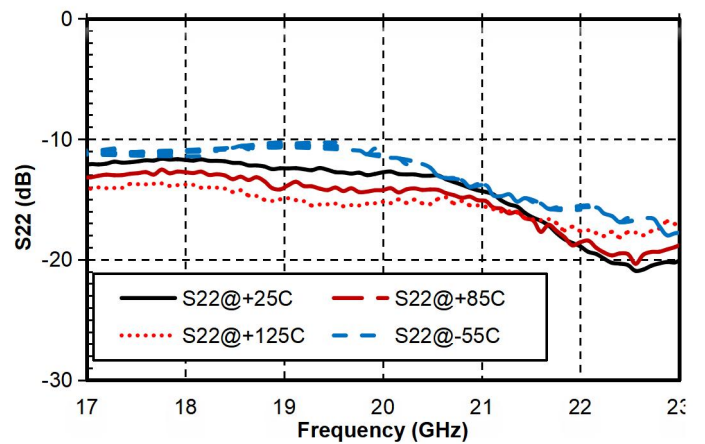
Noise Figure vs. Frequency



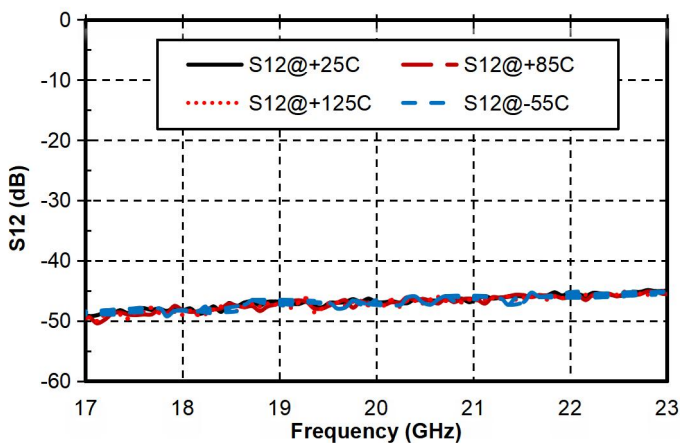
Input Return Loss vs. Frequency



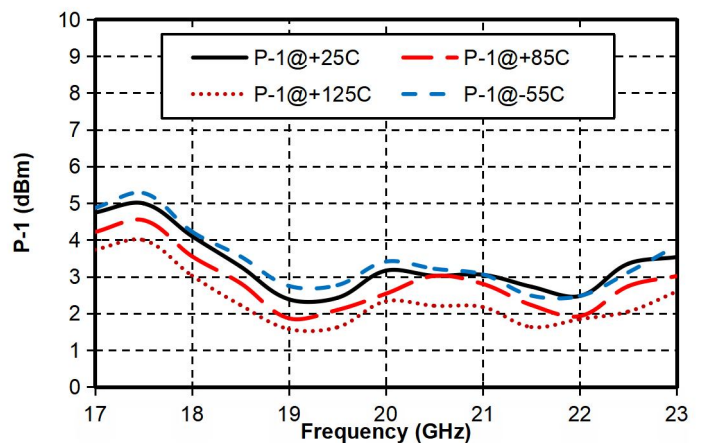
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

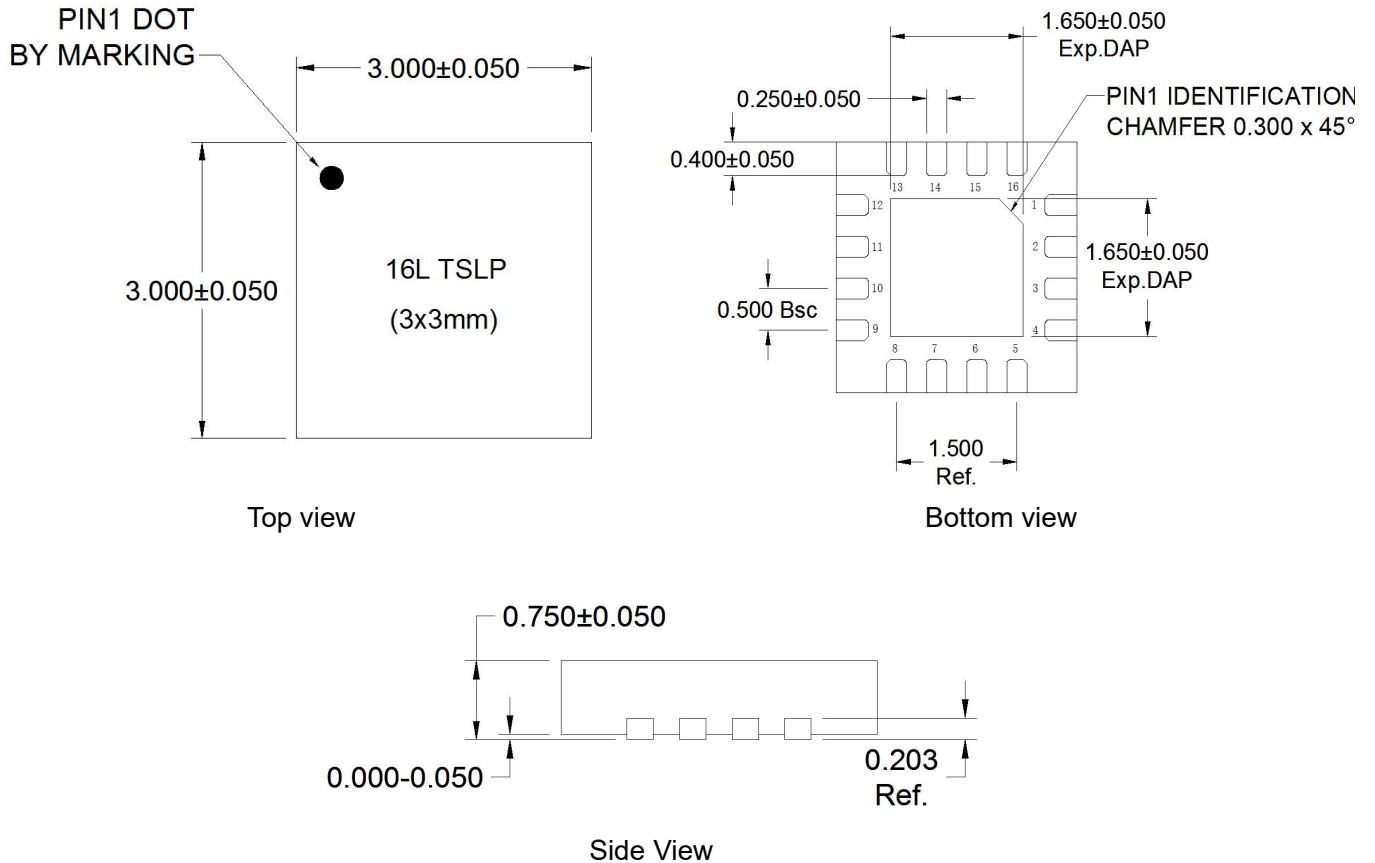


P-1dB vs. Frequency



## GaAs MMIC Low Noise Amplifier Chip, 17 - 23 GHz

### Appearance structure

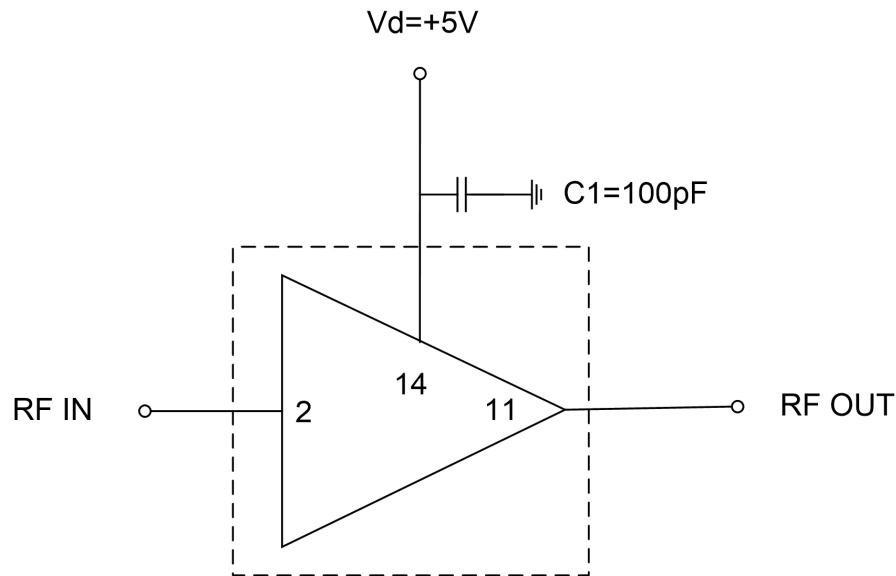


The units in the figure are all millimeters, with a tolerance of  $\pm 0.05$  mm.

Pin Definition		
Solder point number	Function Symbol	Functional Description
2	RF IN	RF signal input terminal, no DC blocking capacitor required
11	RF OUT	RF signal output terminal, no DC blocking capacitor required
14	V d	Amplifier Drain Bias
1, 3, 10, 12	GND	The bottom of the chip needs to be well grounded to RF and DC
4~9, 13, 15, 16	NC	No welding required

## GaAs MMIC Low Noise Amplifier Chip, 17 - 23 GHz

### Recommended Circuit



Raw material	Capacitance, inductance, resistance
C1	100pF

### Precautions for use

- Sealing material : Low-pressure injection molding plastic that meets ROHS specifications
- Lead frame material: copper
- Lead surface plating: nickel palladium gold
- Maximum reflow peak temperature: 260 °C